# Silicon Carbide Schottky Diode

650 V, 20 A

#### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 64 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 qualified

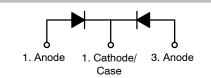
#### **Applications**

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



#### ON Semiconductor®

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#### **Schottky Diode**



TO-247-3LD CASE 340CH

#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code

&3 = Numeric Date Code

K = Lot Code

FFSH2065ADN = Specific Device Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet

#### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted) (per leg)

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)	Single Pulse Avalanche Energy (Note 1)		mJ
I <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 150°C		10* / 20**	А
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	760	А
		T <sub>C</sub> = 150°C, 10 μs	740	А
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	56	А
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	38	А
Ptot	Power Dissipation	T <sub>C</sub> = 25°C	93	W
		T <sub>C</sub> = 150°C	16	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range TO-247 Mounting Torque, M3 Screw		-55 to +175	°C
			60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: \* Per leg, \*\* Per Device

#### THERMAL CHARACTERISTICS

Symbol	Symbol Parameter		Unit
R <sub>0JC</sub> Thermal Resistance, Junction to Case, Max		1.61* / 0.70**	°C/W

NOTE: \* Per leg, \*\* Per Device

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted) (per leg)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 10 A, T <sub>C</sub> = 25°C	-	1.5	1.75	V
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 125°C	-	1.6	2.0	
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 175°C	-	1.72	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 650 V, T <sub>C</sub> = 25°C	-	-	200	μΑ
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 125°C	-	-	400	
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 175°C	-	-	600	
$Q_{C}$	Total Capacitive Charge	V = 400 V	-	34	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	575	-	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	-	62	-	
		V <sub>R</sub> = 400 V, f = 100 kHz	-	47	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **ORDERING INFORMATION**

Part Number	Top Marking	Package	Shipping
FFSH2065ADN-F085	FFSH2065ADN	TO-247-3LD	30 Units / Tube

<sup>1.</sup>  $E_{AS}$  of 64 mJ is based on starting  $T_J = 25$  °C, L = 0.5 mH,  $I_{AS} = 16$  A, V = 50 V.

#### **TYPICAL CHARACTERISTICS**

(T<sub>J</sub> = 25°C unless otherwise noted) (per leg)

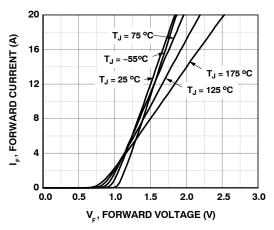


Figure 1. Forward Characteristics

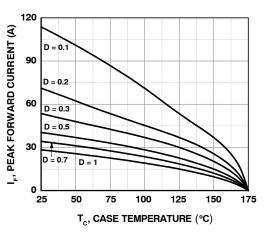


Figure 3. Current Derating

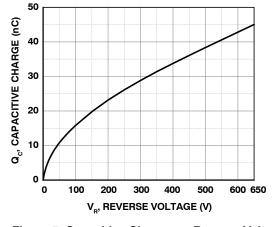


Figure 5. Capacitive Charge vs. Reverse Voltage

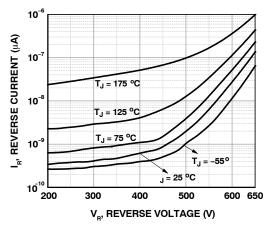


Figure 2. Reverse Characteristics

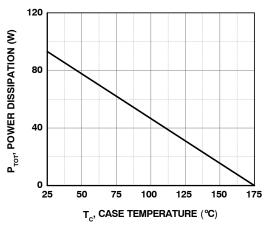


Figure 4. Power Derating

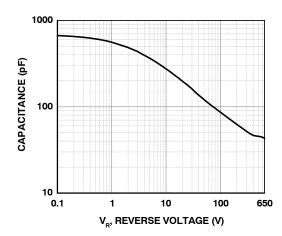


Figure 6. Capacitance vs. Reverse Voltage

#### **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

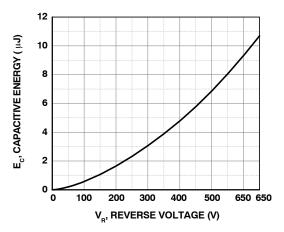


Figure 7. Capacitance Stored Energy

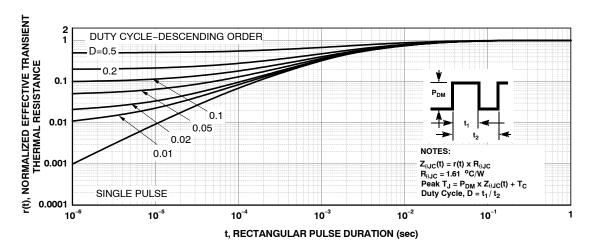


Figure 8. Junction-to-Case Transient Thermal Response Curve

#### **TEST CIRCUIT AND WAVEFORMS**

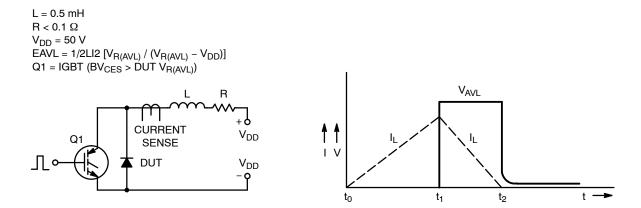
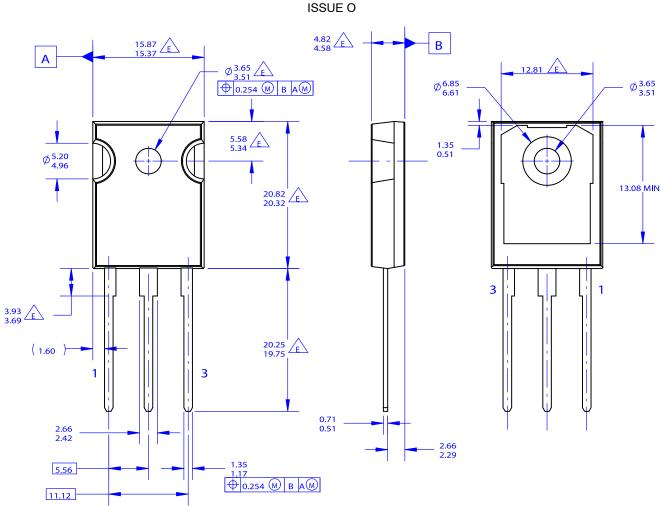


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

#### **PACKAGE DIMENSIONS**

## **TO-247-3LD**CASE 340CH



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 1994

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